TOSHIBA Diode Silicon Epitaxial Planar Type

JDV2S14E

Useful for VCO/TCXO

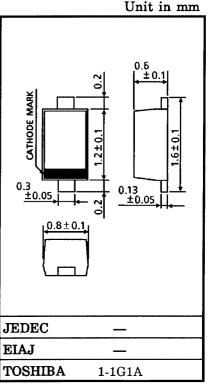
Small Package

High Capacitance Ratio: $C_{1V}/C_{2.5V} = 2.15$ (typ.)

Low Series Resistance : $r_s = 0.4 \Omega$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_{R}	10	٧
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 0.0014 g

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Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse voltage	V _R	$I_R = 1 \mu A$	10	_	_	V
Reverse current	I _R	V _R = 10 V	_	_	3	nA
Capacitance	C _{0.5V}	V _R = 0.5 V, f = 1 MHz	56.3	_	64.7	- pF
	C _{1V}	V _R = 1 V, f = 1 MHz	44	_	49.5	
	C _{2.5V}	V _R = 2.5 V, f = 1 MHz	19	_	26.5	
	C _{4V}	V _R = 4 V, f = 1 MHz	9.2	_	12	
Capacitance ratio	C _{0.5V} /C _{1V}	_	1.25	_	1.35	_
	C _{1V} /C _{2.5V}	_	1.99	2.15	2.3	
Series resistance	r _s	V _R = 4 V, f = 100 MHz	_	0.4	0.8	Ω

Note: Signal level when capacitance is measured. $V_{\text{sig}} = 500 \text{ mV}_{\text{rms}}$

Marking



